



# FDS86141

## N-Channel Power Trench<sup>®</sup> MOSFET

100 V, 7 A, 23 mΩ

### Features

- Max  $r_{DS(on)}$  = 23 mΩ at  $V_{GS} = 10\text{ V}$ ,  $I_D = 7\text{ A}$
- Max  $r_{DS(on)}$  = 36 mΩ at  $V_{GS} = 6\text{ V}$ ,  $I_D = 5.5\text{ A}$
- High performance trench technology for extremely low  $r_{DS(on)}$
- 100% UIL Tested
- RoHS Compliant

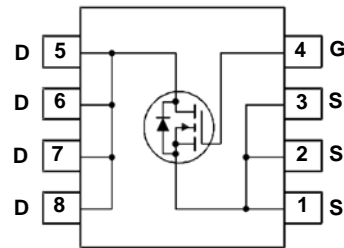
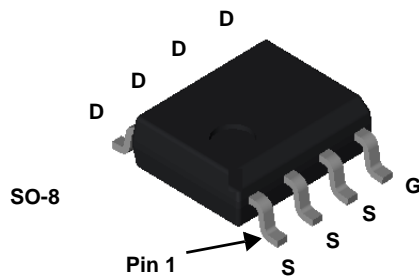


### General Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced Power Trench<sup>®</sup> process that has been especially tailored to minimize the on-state resistance and yet maintain superior switching performance.

### Applications

- DC-DC Conversion



### MOSFET Maximum Ratings $T_A = 25\text{ °C}$ unless otherwise noted

Symbol	Parameter	Rated	Units
$V_{DS}$	Drain to Source Voltage	100	V
$V_{GS}$	Gate to Source Voltage	$\pm 20$	V
$I_D$	Drain Current -Continuous	7	A
	-Pulsed	30	
$E_{AS}$	Single Pulse Avalanche Energy (Note 3)	121	mJ
$P_D$	Power Dissipation $T_A = 25\text{ °C}$ (Note 1a)	2.5	W
	Power Dissipation $T_A = 25\text{ °C}$ (Note 1b)	1.0	
$T_J, T_{STG}$	Operating and Storage Junction Temperature Range	-55 to +150	°C

### Thermal Characteristics

$R_{\theta JC}$	Thermal Resistance, Junction to Case (Note 1)	2.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient (Note 1a)	50	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDS86141	FDS86141	SO-8	13 "	12 mm	2500 units

## Electrical Characteristics $T_J = 25\text{ }^\circ\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Typ	Max	Units
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### Off Characteristics

$BV_{DSS}$	Drain to Source Breakdown Voltage	$I_D = 250\text{ }\mu\text{A}$ , $V_{GS} = 0\text{ V}$	100			V
$\frac{\Delta BV_{DSS}}{\Delta T_J}$	Breakdown Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		67		mV/ $^\circ\text{C}$
$I_{DSS}$	Zero Gate Voltage Drain Current	$V_{DS} = 80\text{ V}$ , $V_{GS} = 0\text{ V}$			1	$\mu\text{A}$
$I_{GSS}$	Gate to Source Leakage Current	$V_{GS} = \pm 20\text{ V}$ , $V_{DS} = 0\text{ V}$			$\pm 100$	nA

### On Characteristics

$V_{GS(th)}$	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}$ , $I_D = 250\text{ }\mu\text{A}$	2	3.1	4	V
$\frac{\Delta V_{GS(th)}}{\Delta T_J}$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D = 250\text{ }\mu\text{A}$ , referenced to $25\text{ }^\circ\text{C}$		-10		mV/ $^\circ\text{C}$
$r_{DS(on)}$	Static Drain to Source On Resistance	$V_{GS} = 10\text{ V}$ , $I_D = 7\text{ A}$		19	23	m $\Omega$
		$V_{GS} = 6\text{ V}$ , $I_D = 5.5\text{ A}$		27	37	
		$V_{GS} = 10\text{ V}$ , $I_D = 7\text{ A}$ , $T_J = 125\text{ }^\circ\text{C}$		33	40	
$g_{FS}$	Forward Transconductance	$V_{DS} = 10\text{ V}$ , $I_D = 7\text{ A}$		19		S

### Dynamic Characteristics

$C_{iss}$	Input Capacitance	$V_{DS} = 50\text{ V}$ , $V_{GS} = 0\text{ V}$ , $f = 1\text{ MHz}$		703	934	pF
$C_{oss}$	Output Capacitance			186	247	pF
$C_{rss}$	Reverse Transfer Capacitance			8.6	13	pF
$R_g$	Gate Resistance			0.5		$\Omega$

### Switching Characteristics

$t_{d(on)}$	Turn-On Delay Time	$V_{DD} = 50\text{ V}$ , $I_D = 7\text{ A}$ , $V_{GS} = 10\text{ V}$ , $R_{GEN} = 6\text{ }\Omega$		8.3	17	ns
$t_r$	Rise Time			3.2	10	ns
$t_{d(off)}$	Turn-Off Delay Time			14.3	26	ns
$t_f$	Fall Time			3.2	10	ns
$Q_{g(TOT)}$	Total Gate Charge		$V_{GS} = 0\text{ V to }10\text{ V}$		11.8	16.5
	Total Gate Charge	$V_{GS} = 0\text{ V to }5\text{ V}$	$V_{DD} = 50\text{ V}$ $I_D = 7\text{ A}$	6.7	9.4	nC
$Q_{gs}$	Total Gate Charge			3.4		nC
$Q_{gd}$	Gate to Drain "Miller" Charge			3.1		nC

### Drain-Source Diode Characteristics

$V_{SD}$	Source to Drain Diode Forward Voltage	$V_{GS} = 0\text{ V}$ , $I_S = 7\text{ A}$ (Note 2)		0.8	1.3	V
		$V_{GS} = 0\text{ V}$ , $I_S = 2\text{ A}$ (Note 2)		0.8	1.2	
$t_{rr}$	Reverse Recovery Time	$I_F = 7\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$		43	69	ns
$Q_{rr}$	Reverse Recovery Charge			39	62	nC

#### NOTES:

1.  $R_{\theta JA}$  is determined with the device mounted on a 1 in<sup>2</sup> pad 2 oz copper pad on a 1.5 x 1.5 in. board of FR-4 material.  $R_{\theta JC}$  is guaranteed by design while  $R_{\theta CA}$  is determined by the user's board design.



a) 50  $^\circ\text{C}/\text{W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper.

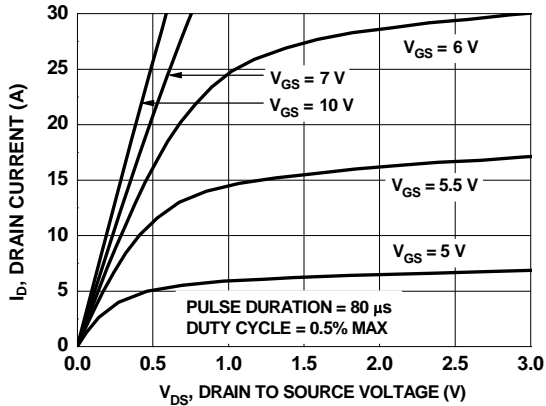


b) 125  $^\circ\text{C}/\text{W}$  when mounted on a minimum pad.

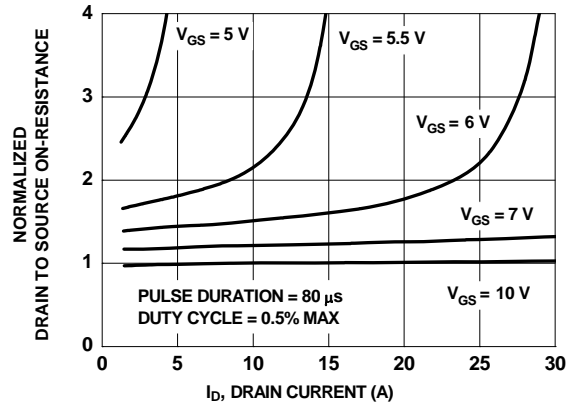
2. Pulse Test: Pulse Width < 300  $\mu\text{s}$ , Duty cycle < 2.0 %.

3. Starting  $T_J = 25\text{ }^\circ\text{C}$ ; N-ch: L = 3 mH,  $I_{AS} = 9\text{ A}$ ,  $V_{DD} = 100\text{ V}$ ,  $V_{GS} = 10\text{ V}$ .

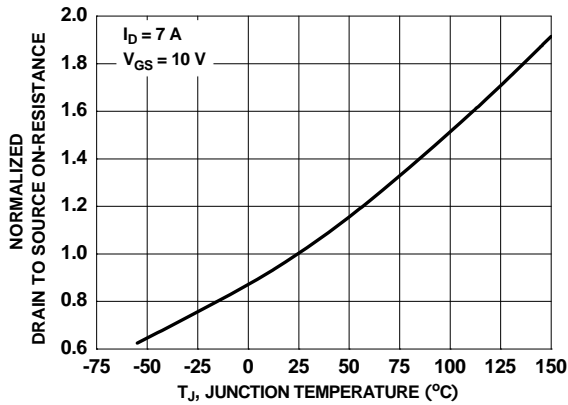
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



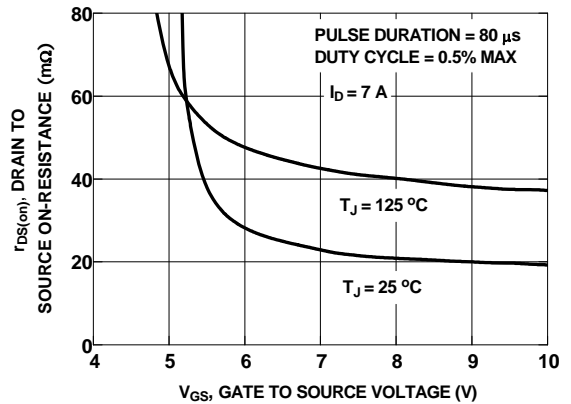
**Figure 1. On-Region Characteristics**



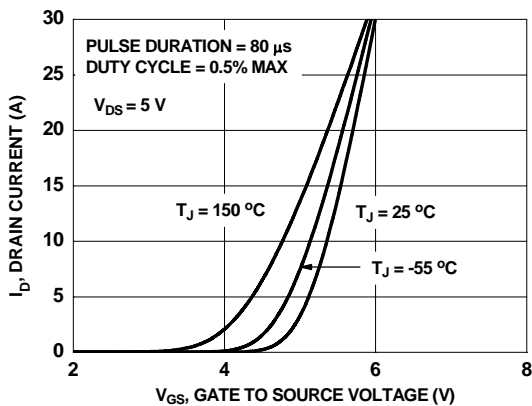
**Figure 2. Normalized On-Resistance vs Drain Current and Gate Voltage**



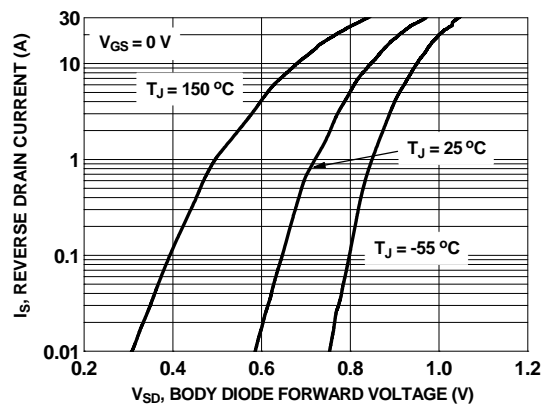
**Figure 3. Normalized On-Resistance vs Junction Temperature**



**Figure 4. On-Resistance vs Gate to Source Voltage**

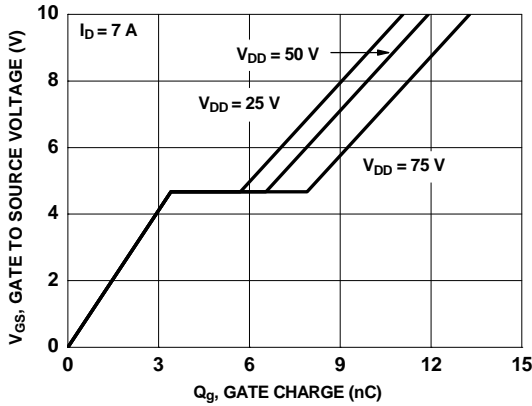


**Figure 5. Transfer Characteristics**

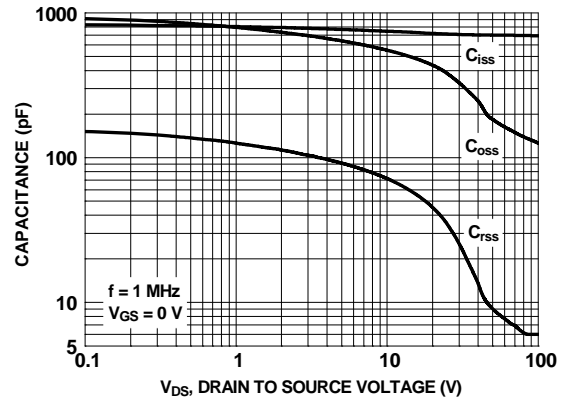


**Figure 6. Source to Drain Diode Forward Voltage vs Source Current**

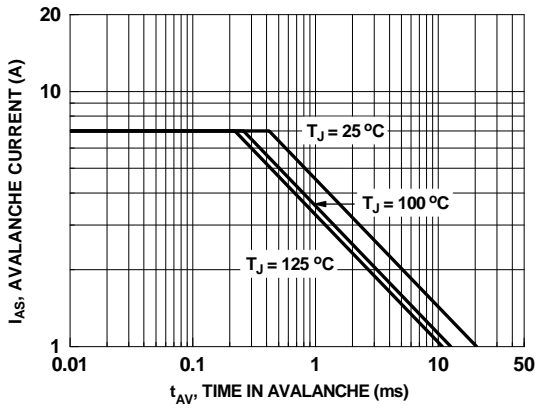
**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



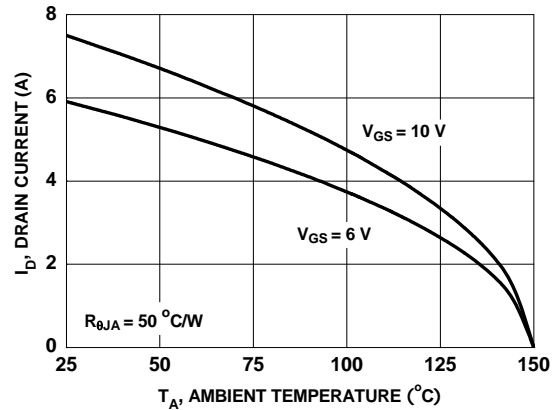
**Figure 7. Gate Charge Characteristics**



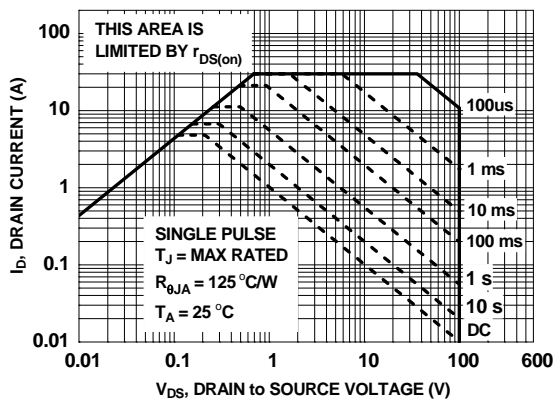
**Figure 8. Capacitance vs Drain to Source Voltage**



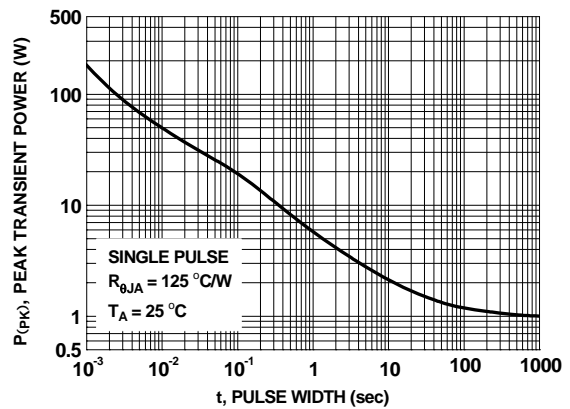
**Figure 9. Unclamped Inductive Switching Capability**



**Figure 10. Maximum Continuous Drain Current vs Ambient Temperature**

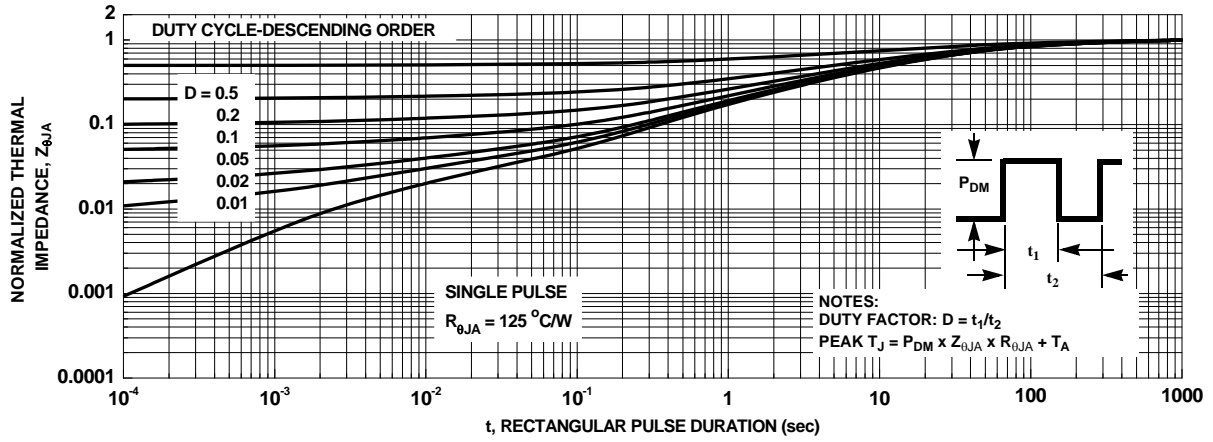


**Figure 11. Forward Bias Safe Operating Area**

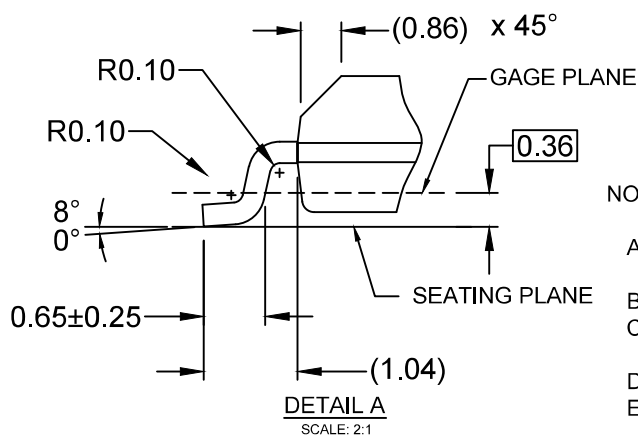
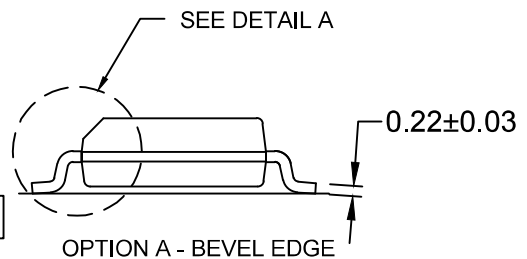
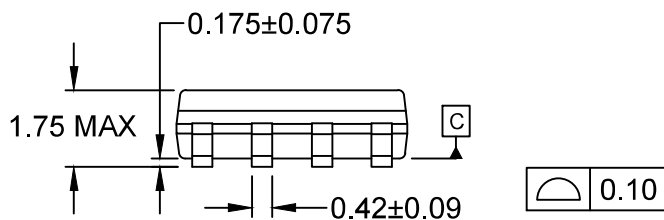
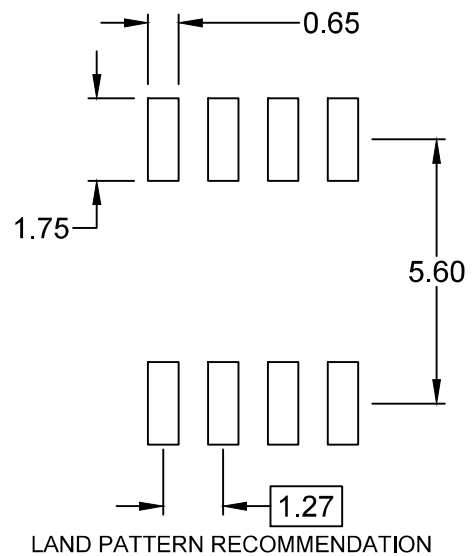
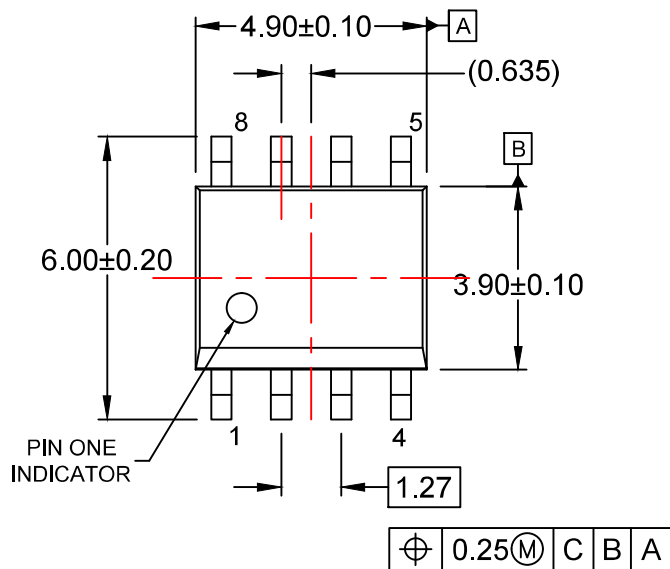


**Figure 12. Single Pulse Maximum Power Dissipation**

**Typical Characteristics**  $T_J = 25\text{ }^\circ\text{C}$  unless otherwise noted



**Figure 13. Junction-to-Ambient Transient Thermal Response Curve**



NOTES:

- A) THIS PACKAGE CONFORMS TO JEDEC MS-012, VARIATION AA.
- B) ALL DIMENSIONS ARE IN MILLIMETERS.
- C) DIMENSIONS DO NOT INCLUDE MOLD FLASH OR BURRS.
- D) LANDPATTERN STANDARD: SOIC127P600X175-8M
- E) DRAWING FILENAME: M08Arev16



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